



**SOT-89-3L Plastic-Encapsulate Transistors**

**2SA1662** TRANSISTOR (PNP)

**FEATURES**

Complementary to KTC4374

**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

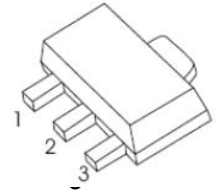
Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	-80	V
V <sub>CE0</sub>	Collector-Emitter Voltage	-80	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current -Continuous	-0.4	A
P <sub>C</sub>	Collector Power Dissipation	0.5	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55-150	°C

**SOT-89-3L**

1. BASE

2. COLLECTOR

3. EMITTER



**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-1mA, I <sub>E</sub> =0	-80			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-10mA, I <sub>B</sub> =0	-80			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-1mA, I <sub>C</sub> =0	-5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-80V, I <sub>E</sub> =0			-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-5V, I <sub>C</sub> =0			-0.1	μA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =-2V, I <sub>C</sub> =-50mA	70		240	
	h <sub>FE(2)</sub>	V <sub>CE</sub> =-2V, I <sub>C</sub> =-200mA	40			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-200mA, I <sub>B</sub> =-20mA			-0.4	V
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> =-2V, I <sub>C</sub> =-5mA	-0.55		-0.8	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-10V, I <sub>C</sub> =-10mA		120		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, I <sub>E</sub> =0, f=1MHz		14		pF

**CLASSIFICATION OF h<sub>FE(1)</sub>**

Rank	O	Y
Range	70-140	120-240
Marking	FO	FY